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Concl.

a second single crystal substrate portion having active devices formed thereon and defining a device surface wherein the dielectric layer of the first substrate portion is bonded to the device surface of the second substrate portion, wherein selected ones of said active devices of said second substrate portion are intercoupled via metal lines,

wherein said metal lines, intercoupling said active devices formed on said second single crystal substrate portion, are unimpaired by heat during fabrication.

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31. (Amended Twice) An apparatus comprising:

a primary substrate having a first level of devices formed thereon and defining a device surface; and

at least one secondary single crystal substrate coupled to the device surface, the at least one secondary substrate having active devices formed thereon and selected ones of said active devices of said at least one secondary single crystal substrate are intercoupled via metal lines,

wherein said metal lines, intercoupling said active devices formed on said at least one secondary single crystal substrate, are unimpaired by heat during fabrication.